

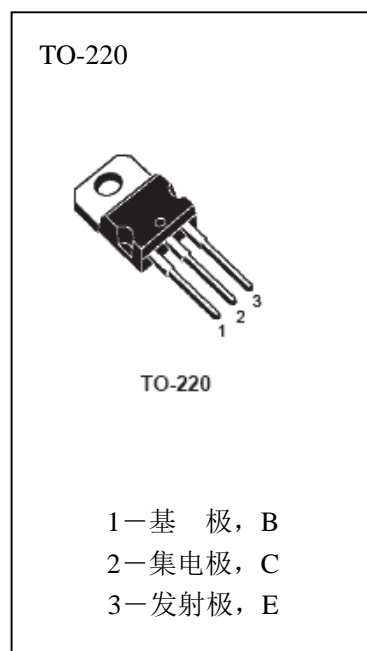
主要用途

该器件为达林顿三极管内含阻尼二极管，用于高增益电路。

极限值 (T_a=25℃)

T _{stg}	— 贮存温度	-65~150℃
T _j	— 结温	150℃
P _C	— 集电极耗散功率 (T _c =25℃)	65W
P _C	— 集电极耗散功率 (T _A =25℃)	2WV
V _{CB0}	— 集电极—基极电压	-100VV
V _{CEO}	— 集电极—发射极电压	-100VV
V _{EB0}	— 发射极—基极电压	-5V
I _C	— 集电极电流	-A
I _{CP}	— 集电极电流 (脉冲)	-8A
I _B	— 基极电流	-120mA

外形图及引脚排列



电参数 (T_a=25℃)

参数符号	符 号 说 明	最小值	典型值	最大值	单 位	测 试 条 件
V _{CB0}	集电极—基极击穿电压	-100			V	I _C =1mA, I _E =0
V _{CEO}	集电极—发射极击穿电压	-100			V	I _C =5mA, I _B =0
I _{CEO}	集电极—发射极截止电流			-0.5	mA	V _{CE} =50V, I _B =0
I _{CB0}	集电极—基极截止电流			-0.2	mA	V _{CB} =100V, I _E =0
I _{EB0}	发射极—基极截止电流			-2.0	mA	V _{EB} =5V, I _C =0
HFE	直流电流增益	1000				V _{CE} =3V, I _C =0.5A
V _{CE(sat1)}	集电极—发射极饱和电压			-2.0	V	I _C =3A, I _B =12mA
V _{CE(sat2)}				-4.0	V	I _C =5A, I _B =20mA
V _{BE(on)}	基极—发射极导通电压			-2.5	V	V _{CE} =3V, I _C =3A
C _{ob}	共基极输出电容			-200	pF	V _{CB} =10V, I _E =0, f=0.1MHz

■ 特性曲线

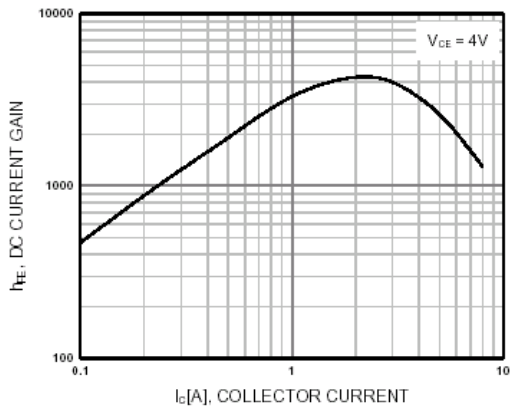


Figure 1. DC current Gain

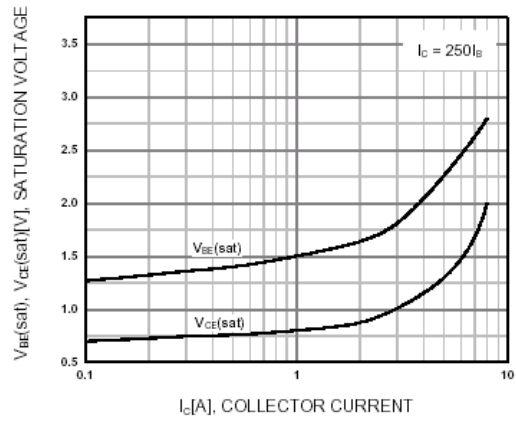


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

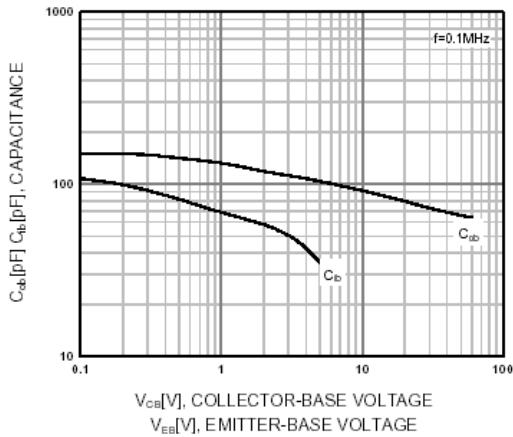


Figure 3. Output and Input Capacitance
vs. Reverse Voltage

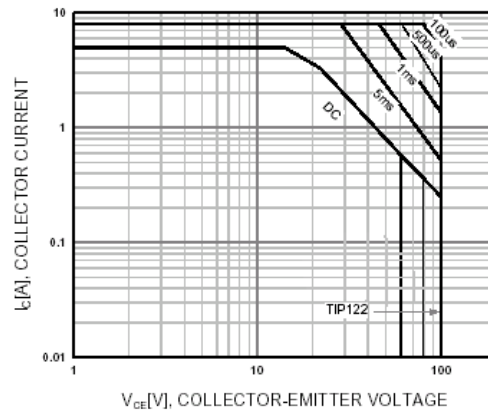


Figure 4. Safe Operating Area

